## [STRUCTURE OF A MEMORY DEVICE AND FABRICATION METHOD THEREOF]

## **Abstract of Disclosure**

A buried bit line and a fabrication method thereof, wherein the device includes a substrate, a shallow doped region disposed in the substrate, a deep doped region disposed in the substrate below a part of the shallow doped region, wherein the shallow doped region and the deep dope region together form a bit line of the memory device.

Figures